SCS302AH

SiC Schottky Barrier Diode

Datasheet

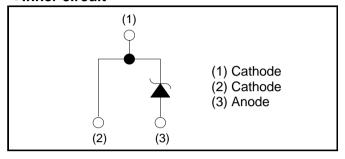
V_R	650V
I _F	2A
Q_{C}	6nC

Outline TO-220ACP (1) (2) (3)

Features

- 1) Shorter recovery time
- 2) Reduced temperature dependence
- 3) High-speed switching possible
- 4) High surge current capability

•Inner circuit



Packaging specifications

	Packaging	Tube
	Reel size (mm)	-
Type	Tape width (mm)	-
Туре	Basic ordering unit (pcs)	50
	Packing code	C9
	Marking	SCS302AH

Construction

Silicon carbide epitaxial planar type

• Absolute maximum ratings $(T_i = 25^{\circ}C)$

•Absolute maximum ratings $(T_j = 25 \text{ C})$				
Parameter		Symbol	Value	Unit
Reverse voltage (re	petitive peak)	V_{RM}	650	V
Reverse voltage (DC)		V_R	650	V
Continuous forward	current (T _c = 145°C)	I _F	2.15	А
Surge non-	PW=10ms sinusoidal, T _j =25°C		19	А
repetitive forward current	PW=10ms sinusoidal, T _j =150°C	I _{FSM}	16	А
	PW=10μs square, T _j =25°C		70	А
Repetitive peak forward current		I _{FRM}	12 ^{*1}	А
1≦PW≦10ms, T _j =25°C		۲ ،2 _۱ ،	1.8	A ² s
i ² t value	1≦PW≦10ms, T _j =150°C	$\int i^2 dt$	1.2	A ² s
Total power disspation		P_{D}	22 *2	W
Junction temperature		T _j	175	°C
Range of storage temperature		T _{stg}	-55 to +175	°C

^{*1} T_c=100°C, T_j=150°C, Duty cycle=10% *2 T_c=25°C

●Electrical characteristics (T_i = 25°C)

Parameter	Symbol	Conditions	Values			l loit
			Min.	Тур.	Max.	Unit
DC blocking voltage	V_{DC}	I _R =10.8μA	650	-	-	V
	V _F	I _F =2A,T _j =25°C	-	1.35	1.50	V
Forward voltage		I _F =2A,T _j =150°C	-	1.44	1.71	V
		I _F =2A,T _j =175°C	-	1.50	-	V
Reverse current	I _R	V _R =650V,T _j =25°C	-	0.0065	10.8	μΑ
		V _R =650V,T _j =150°C	-	0.43	43	μΑ
		V _R =650V,T _j =175°C	-	1.29	-	μΑ
Total capacitance	С	V _R =1V,f=1MHz	-	110	-	pF
		V _R =650V,f=1MHz	-	10	-	pF
Total capacitive charge	Q _C	V _R =400V,di/dt=350A/μs	-	6	-	nC
Switching time	t _C	V _R =400V,di/dt=350A/μs	-	11	-	ns
Non-repetetive Avaranche Energy	E _{ava}	L=1mH	-	18	-	mJ

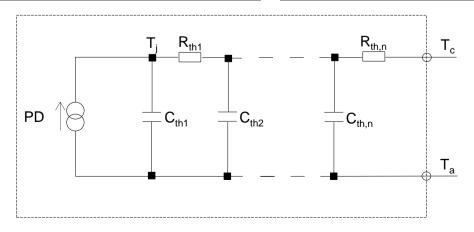
Thermal characteristics

Parameter	Parameter Symbol Cor	Conditions	Values			Unit
Parameter		Conditions	Min.	Тур.	Max.	Offic
Thermal resistance	$R_{th(j-c)}$	-	-	4.5	6.7	K/W

●Typical Transient Thermal Characteristics

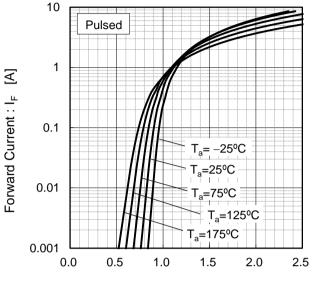
Symbol	Value	Unit
R _{th1}	8.21×10 ⁻²	
R _{th2}	5.99×10 ⁻¹	K/W
R _{th3}	3.80×10 ⁰	

Symbol	Value	Unit
C_{th1}	6.35×10 ⁻⁵	
C_{th2}	2.10×10 ⁻⁴	Ws/K
C_{th3}	8.17×10 ⁻⁴	



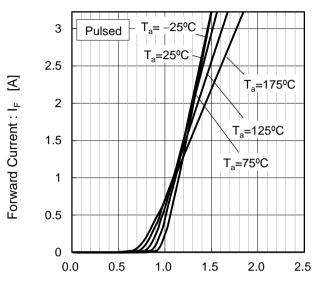
•Electrical characteristic curves

Fig.1 V_F - I_F Characteristics



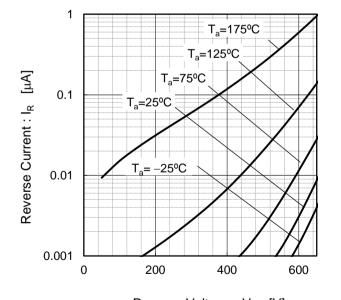
Forward Voltage : V_F [V]

Fig.2 V_F - I_F Characteristics



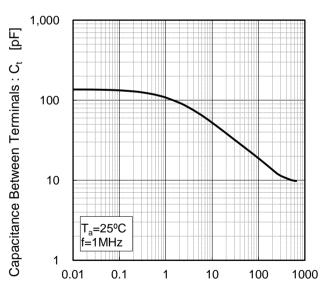
Forward Voltage : V_F [V]

Fig.3 V_R - I_R Characteristics



Reverse Voltage : V_R [V]

Fig.4 V_R-C_t Characteristics



Reverse Voltage : V_R [V]

• Electrical characteristic curves

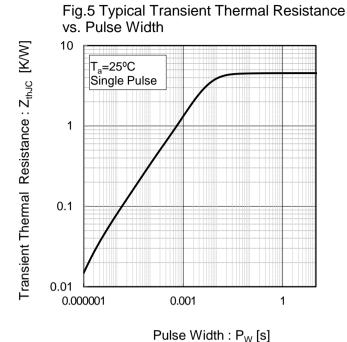


Fig.6 Power Dissipation

25
20
15
10
5

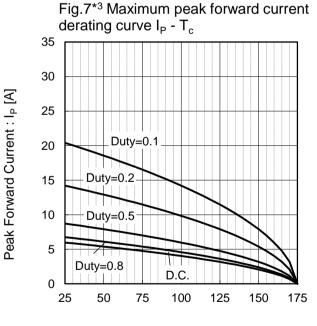
Case Temperature : T_c [°C]

125

150

175

100



Case Temperature : T_c [°C] *3 Based on max Vf, max $R_{th(j-c)}$ Valid for switching of above 10kHz, excluding D.C. curve.

Fig.8*4 Typical peak forward current derating curve I_P - T_c (Not guaranteed) 30 Duty=0.1 25 Duty=0.2 20 15 Duty=0.5 10 5 Duty=0.8 D.C. 0 25 50 75 100 125 150 175

Case Temperature : T_c [°C] *4 Based on typ Vf, typ $R_{th(j-c)}$ Typical value, not guaranteed Valid for switching of above 10kHz, excluding D.C. curve

Peak Forward Current: Ip [A]

Power Dissipation [W]

0

25

50

75

Electrical characteristic curves

vs. Pulse width (Sinusoidal waveform) Surge non-repetitive forward current : I_{FSM} [A] 100 T_a=25°C Single Pulse

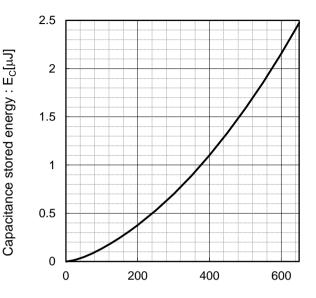
Fig.9 Surge non-repetitive forward current

Pulse Width: Pw [s]

0.001

0.01

Fig.10 Typical capacitance store energy



Reverse Voltage: V_R [V]

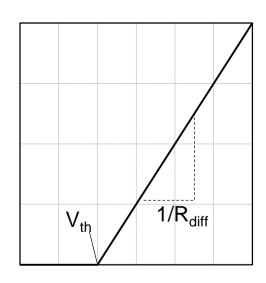
Symplified forward characteristic model

0.0001

0.00001

Forward Current: IF

Fig.11 Equivalent forward current curve



Forward Voltage: V_F

$$V_F = V_{th} + R_{diff} I_F$$

$$\begin{aligned} &V_{th} \left(\ T_{j} \ \right) = a_{0} + a_{1} \, T_{j} \\ &R_{diff} \left(\ T_{j} \ \right) = b_{0} + b_{1} \, T_{j} + b_{2} \, T_{j}^{2} \end{aligned}$$

Symbol	Typical Value	Unit
a_0	9.66×10 ⁻¹	V
a ₁	-1.1×10 ⁻³	V/°C
b ₀	1.64×10 ⁻¹	Ω
b ₁	3.47×10 ⁻⁴	Ω/°C
b ₂	3.57×10 ⁻⁶	Ω /°C ²

 T_i in °C; -55 °C < T_i < 175°C; I_F < 4 A

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